



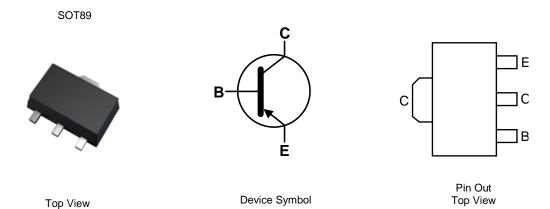
32V PNP POWER SWITCHING TRANSISTOR IN SOT89

Features

- BV_{CEO} > -32V
- I_C = -1A High Continuous Collector Current
- Complementary NPN Type: 2DD1664
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.055 grams (Approximate)



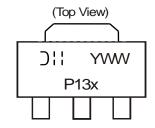
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DB1132P-13	P13P	13	12	2,500
2DB1132Q-13	P13Q	13	12	2,500
2DB1132R-13	P13R	13	12	2,500
2DB1132R-13R	P13R	13	12	4,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Oll = Manufacturer's Marking P13x = Product Type Marking Code: Where P13P = 2DB1132P

Where P13P = 2DB1132P P13Q = 2DB1132Q

P13R = 2DB1132R YWW = Date Code Marking

Y = Last Digit of Year (ex: 9 = 2019) WW = Week Code (01 to 52)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	P_{D}	1.5	W	
	(Note 7)		2.0	ı	
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	83	°C/W	
	(Note 7)		60]	
Thermal Resistance, Junction to Case	(Note 5)	$R_{ heta JC}$	18	°C/W	
Thermal Resistance, Junction to Lead (Note 8)		$R_{ heta JL}$	22	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

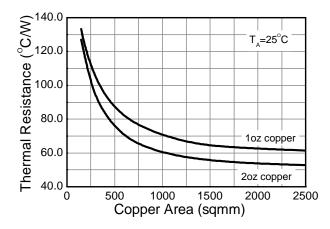
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

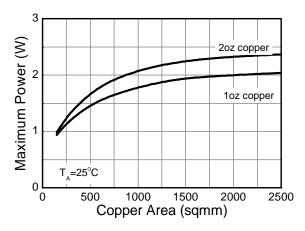
Notes:

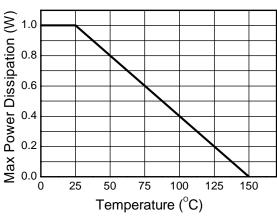
- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

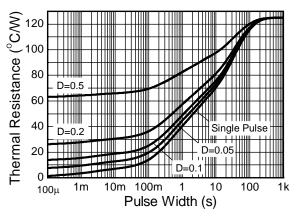


Thermal Characteristics and Derating Information



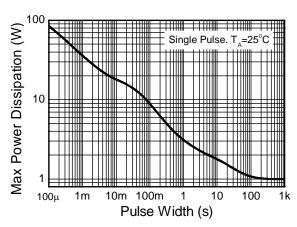






Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation

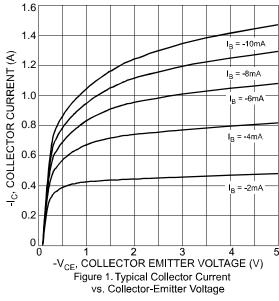


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-40	_	_	V	I _C = -50μA
Collector-Emitter Breakdown Voltag	ge (Note 10)	BV _{CEO}	-32	_	_	V	I _C = -1mA
Emitter-Base Breakdown Voltage		BV _{EBO}	-5	_	_	V	I _E = -50μA
Collector Cut-Off Current		I _{CBO}	_		-0.5	μΑ	V _{CB} = -20V
Emitter Cut-Off Current		I _{EBO}	_	_	-0.5	μΑ	V _{EB} = -4V
Static Forward Current Transfer	2DB1132P		82		180		
Ratio (Note 10)	2DB1132Q	h_{FE}	120	_	270		$I_C = -100 \text{mA}, V_{CE} = -3 \text{V}$
Italio (Note 10)	2DB1132R		180		390		
Collector-Emitter Saturation Voltage (Note 10)		V _{CE(SAT)}	_	-125	-500	mV	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Transition Frequency		f⊤	_	190	_	MHz	$I_E = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 30 MHz
Output Capacitance		C_ob	_	12	30	pF	$I_E = 0A$, $V_{CB} = -10V$, $f = 1MHz$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



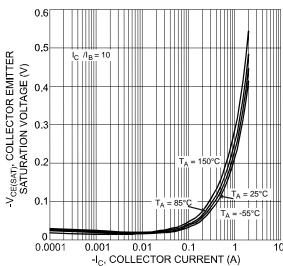
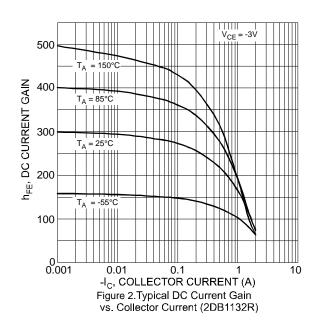
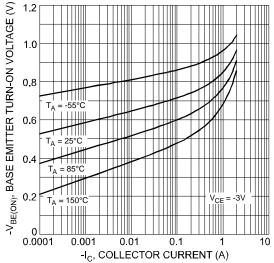


Figure 3.Typical Collector-Emitter Saturation Voltage vs. Collector Current





-I_C, COLLECTOR CURRENT (A)
Figure 4. Typical Base-Emitter Turn-On Voltage
vs. Collector Current



Typical Electrical Characteristics (continued) (@T_A = +25°C, unless otherwise specified.)

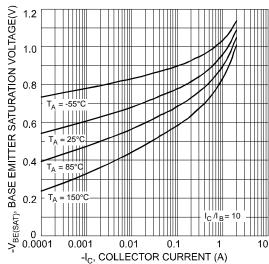


Figure 5. Typical Base-Emitter Saturation Voltage vs. Collector Current

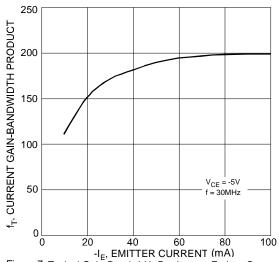
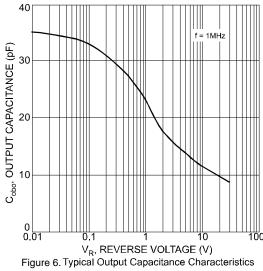


Figure 7. Typical Gain-Bandwidth Product vs. Emitter Current

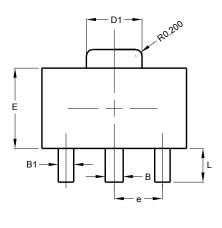


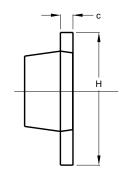


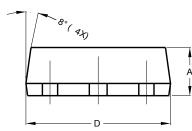
Package Outline Dimensions

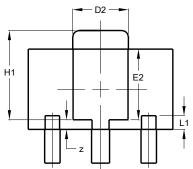
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







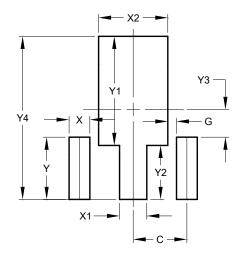


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value
Dimensions	(in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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